









CEU12N10

100V Δ 150mΩ Δ 11A Δ Si MOSFET

SILICON Si MOSFET ▲ SMD type

N-channel enhancement mode

UL94V-0 rated flame retardant epoxy

TO252 (DPAK) package ▲ MSL 3

Super high dense cell density for extremely low R_{DS(ON)}

High power and current handling capability

MAXIMUM RATINGS

Parameter (T_c = 25°C, unless otherwise noted)		Characteristics
Drain-Source Voltage	V _{DS}	100V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current at T _C = 25°C	I _D	11A
Pulsed Drain Current Note 1	I _{DM} Note4	44A
Maximum Power Dissipation at T _C = 25°C	P _D	43W
Power Dissipation Derating above 25°C	ΔP _D	0.29W/°C
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +175°C

THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	3.5°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH_JA}	50°C/W

APPLICATIONS

Battery Management Systems	E-Bike	Industrial Control	Power Inverter	UPS
+4-	50			= =

PIN DESCRIPTION

Circuit Diagram	Outline • Bottom View	Pin No.	Description
G (3) S (2)	3 2	1 2 3	Drain Source Gate



ELECTRICAL CHARACTERISTICS ▲ T_C = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = 250\mu A$	BV_{DSS}	100			V
Zero Gate Voltage Drain Current	$V_{DS} = 100V, V_{GS} = 0V$	I _{DSS}			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	I _{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_{D} = 250 \mu A$	$V_{GS(th)}$	2		4	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 6A$	R _{DS(ON)}		150	180	mΩ
Forward Transconductance	$V_{DS} = 10V$, $I_{D} = 6A$	g FS		5		S
Dynamic Characteristics Note 3						
Input Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, $f = 1MHz$	C _{ISS}		430		pF
Output Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, $f = 1MHz$	Coss		90		pF
Reverse Transfer Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, $f = 1MHz$	C_{RSS}		20		pF
Switching Characteristics Note 3						
Turn-On Delay Time	V_{DD} = 80V, V_{GS} = 10V, I_{D} = 11A, $R_{G(ext)}$ = 9.1 Ω	t _{D(ON)}		12	24	ns
Turn-On Rise Time	V_{DD} = 80V, V_{GS} = 10V, I_D = 11A, $R_{G(ext)}$ = 9.1 Ω	t_R		7	14	ns
Turn-Off Delay Time	V_{DD} = 80V, V_{GS} = 10V, I_D = 11A, $R_{G(ext)}$ = 9.1 Ω	t _{D(OFF)}		18	35	ns
Turn-Off Fall Time	V_{DD} = 80V, V_{GS} = 10V, I_{D} = 11A, $R_{G(ext)}$ = 9.1Ω	t_{\scriptscriptstyleF}		3	6	ns
Total Gate Charge	$V_{DS} = 80V$, $V_{GS} = 10V$, $I_{D} = 11A$	Q_{G}		8	16	nC
Gate Source Charge	$V_{DS} = 80V$, $V_{GS} = 10V$, $I_{D} = 11A$	Q_{GS}		1.5		nC
Gate Drain Charge	$V_{DS} = 80V$, $V_{GS} = 10V$, $I_D = 11A$	Q_{GD}		2		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current		Is			11	Α
Drain-Source Diode Forward Voltage Note 2	$V_{GS} = 0V$, $I_S = 11A$	V_{SD}			1.2	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 3: Guaranteed by design, not subject to production testing.
- 4: L = 0.1mH, I_{AS} = 10A, V_{DD} = 25V, R_G = 25Ω, Starting T_J = 25°C



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



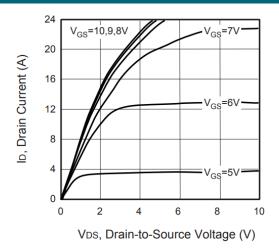


Fig. 2 • Transfer Characteristics

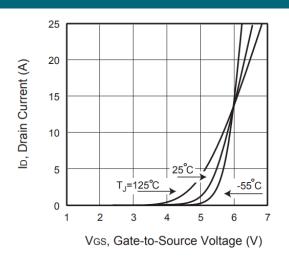


Fig. 3 • Capacitance

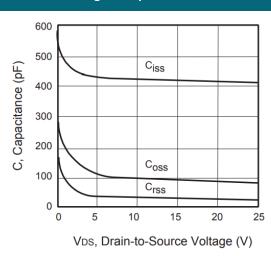


Fig. 4 • On-Resistance Variation with Temperature

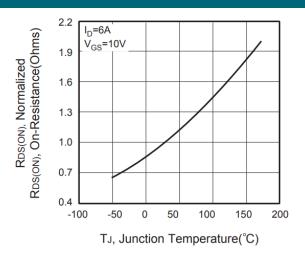


Fig. 5 • Gate Threshold Variation with Temperature

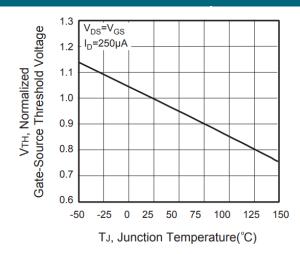
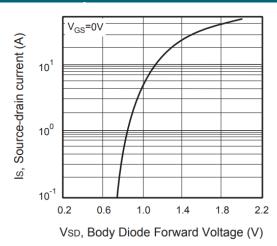


Fig. 6 • Body Diode Forward Voltage Variation with Source Current



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REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

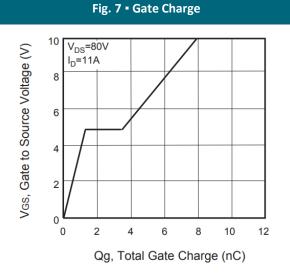


Fig. 8 • Maximum Safe Operating Area

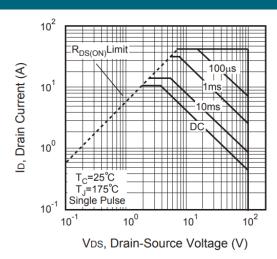
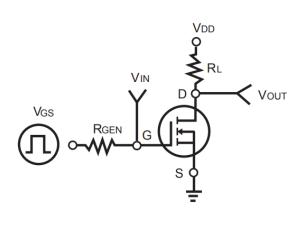


Fig. 9 • Switching Test Circuit

Fig. 10 • Switching Waveforms



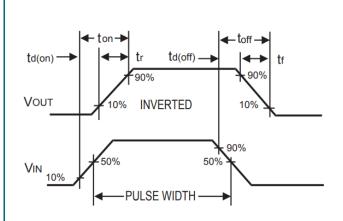
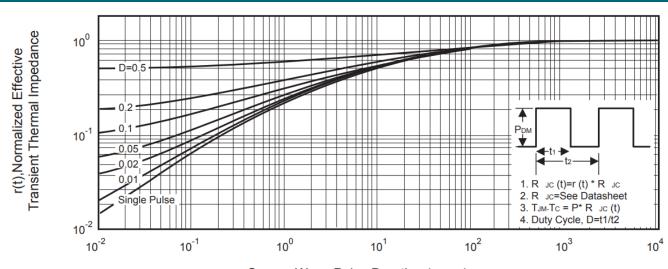


Fig. 11 - Normalized Thermal Transient Impedance Curve

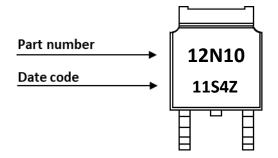


Square Wave Pulse Duration (msec)

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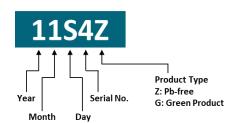


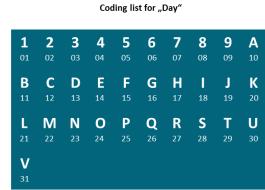
PART MARKING



DATE CODE

Example: 11S4Z

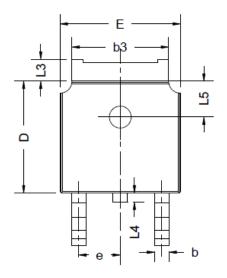


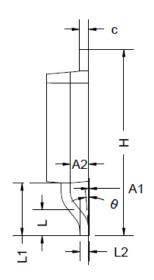


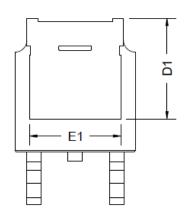


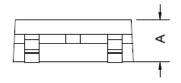


PACKAGE OUTLINE









Sym	Millimeters Millimeters (Min.) (Typ.)		Millimeters (Max.)			
Α	2.20	2.30	2.38			
A1	0.00	-	0.20			
A2	A2 0.90 1.07		1.17			
b	0.68	0.78	0.90			
b3	5.23	5.33	5.46			
С	0.43	0.53	0.61			
D	5.98	6.10	6.22			
D1	5.30 REF					
Е	6.40	6.60	6.73			
E1	4.63	-	-			

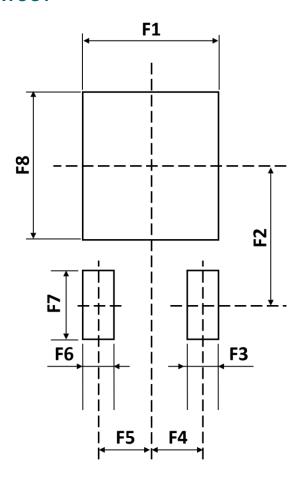
Sym	Millimeters (Min.)								
e		2.286 BSC							
Н	9.40	10.10	10.50						
L	1.38	1.50	1.75						
L1		2.90 REF							
L2		0.51 BSC							
L3	0.88	-	1.28						
L4	0.50		1.00						
L5	1.65	1.80	1.95						
θ	0°	-	8°						

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEU12N10	TO252 (DPAK)	Reel	2,500pcs	5,000pcs	40,000pcs



RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	6.00	-
F2	-	6.25	-
F3	-	1.40	-
F4	-	2.29	-

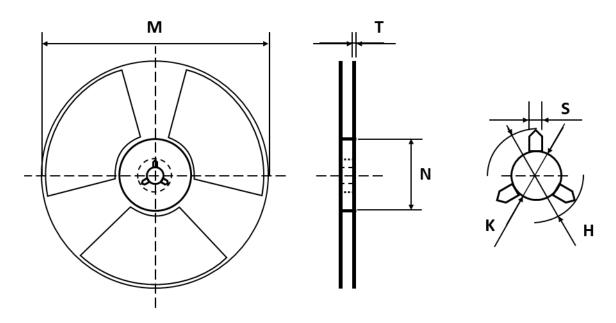
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F5	-	2.29	-
F6	-	1.40	-
F7	-	3.00	-
F8	-	6.50	-

Notes:

- 1. The suggested land pattern dimensions have been provided for reference only.
- 2. For further information, please reference document IPC-7351A.

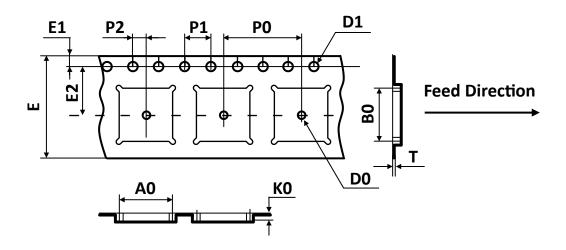


REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
16mm	Ø330	±2.00	±0.50	+0.20	+0 50	+0.50	+0.50
		±2.00	±0.50	±0.20	±0.50	-0.20	-0.20

TAPE DIMENSIONS ▲ All dimensions in mm

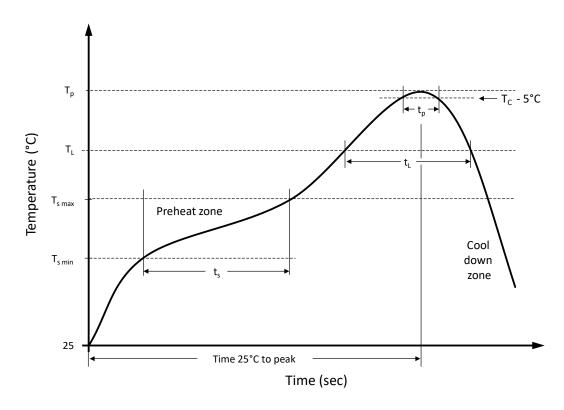


Package	A0	В0	КО	D0	D1	E	E1	E2	P0	P1	P2	Т
TO252	6.90	10.50	2.70	1.50	1.50	16.00	1.75	7.50	8.00	4.00	2.00	0.30
(DPAK)	±0.10	±0.10	±0.10	MIN	±0.10	+0.30	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t _L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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